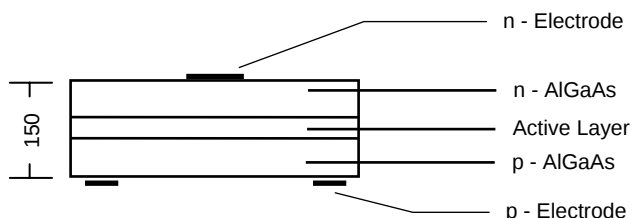
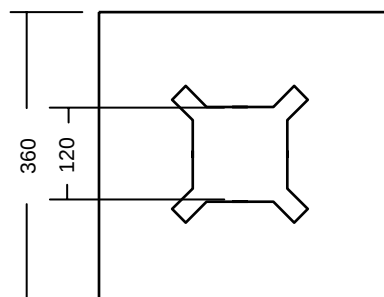


TCS870N



- ❖ Features:
AlGaAs (DHS) / AlGaAs - substrate removed

- ❖ Outline Dimensions:



- ❖ Physical Structure:

Chip dimensions		Chip size	14 mil x 14 mil	360 μm x 360 μm
		Thickness	5.9 mil	150 μm
		Bonding Pad	4.7 mil	120 μm
Electrode	Top	N (cathode)	Gold alloy	
	Backside	P (anode)	Gold alloy	

- ❖ Electro-Optical Characteristics:

Parameter	Symb ol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20\text{mA}$	-	1.35	1.60	V
Reverse Current	I_R	$V_R = 5\text{V}$	-	-	10	μA
Peak Wavelength	λ_P	$I_F = 20\text{mA}$	-	870	-	nm
Output power	P_O	$I_F = 20\text{mA}$	3.8	4.6	-	mW
		$I_F = 50\text{mA}$	9.5	11.5	-	mW
Switching time	t_R, t_F	$I_F = 20\text{mA}$	-	35	-	ns